

電子所演講公告

ENE SEMINAR
ANNOUNCEMENT

GaN HEMT for Power Electronics Applications

演講者：交通大學 張翼 副校長

演講大綱：

Due to high bandgap and high electron mobility, GaN based HEMT devices are now widely studied for power electronics applications.

In this talk, GaN on Si materials growth technique, HEMT device operating theory and GaN HEMT device process technologies will be introduced.

High performance Depletion mode and enhancement mode HEMT devices will be demonstrated.

Finally, performances of several power Electronics modules implementing the developed GaN devices will be presented.

Host：吳孟奇 教授 (Ext 62218)

Location：Delta R215

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